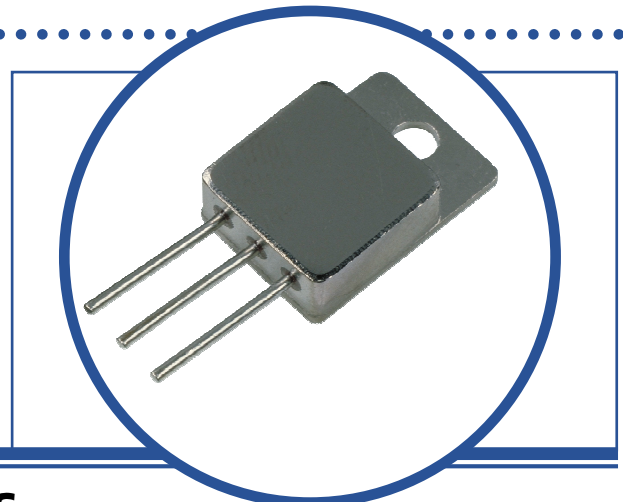


DUAL COMMON CATHODE SILICON CARBIDE SCHOTTKY DIODE

SML20SIC06M3M

- $V_{R(max)} = 600V$
- $I_{F(avg)} = 20A$
- $V_{F(typ)} = 1.8V$
- Metal Hermetic TO-254 Package
- Dual Common Cathode Configuration
- High Reliability Screening Options Available
- Effective Zero Forward and Reverse Recovery



ABSOLUTE MAXIMUM RATINGS ($T_C = 25^\circ C$ (per diode) unless otherwise stated)

V_{RRM}	Peak Repetitive Reverse Voltage	600V
V_{RSM}	Surge Peak Reverse Voltage	600V
$I_{F(AVG)}$	Average Forward Current	20A
I_{FRM}	Repetitive Peak Forward Current ⁽¹⁾ (per diode)	50A
I_{FMAX}	Non-Repetitive Peak Forward Current	250A
P_D	Total Power Dissipation (per diode) at $T_C = 25^\circ C$ Derate Above $T_C = 25^\circ C$	111W 0.56W/ $^\circ C$
T_J	Junction Temperature Range	-55 to +225 $^\circ C$
T_{stg}	Storage Temperature Range	-55 to +225 $^\circ C$

THERMAL PROPERTIES(per diode)

Symbols	Parameters	Max.	Unit
$R_{\theta JC}$	Thermal Resistance, Junction To Case (per Diode)	1.8	$^\circ C/W$

(1) $T_{case} = 25^\circ C$, $T_p = 8.3mS$ Half sine wave $D=0.3$

Beryllium oxide (BeO) HAZARDOUS MATERIAL WARNING

Package containing beryllium oxide must not be ground, machined, or have other processes performed on them which may produce beryllium or beryllium dust.

THESE DEVICES MUST NEVER BE THROWN AWAY WITH GENERAL INDUSTRIAL OR DOMESTIC WASTE.

Semelab Limited reserves the right to change test conditions, parameter limits and package dimensions without notice. Information furnished by Semelab is believed to be both accurate and reliable at the time of going to press. However Semelab assumes no responsibility for any errors or omissions discovered in its use. Semelab encourages customers to verify that datasheets are current before placing orders.



DUAL COMMON CATHODE SILICON CARBIDE SCHOTTKY DIODE



SML20SIC06M3M

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise stated Per Side)

Symbol	Parameters	Test Conditions	Min.	Typ.	Max.	Unit
V _F ⁽¹⁾	Diode Forward Voltage	I _F = 12A		1.5	2	V
		I _F = 20A		1.8	2.5	
		I _F = 20A T _J = 175°C		2.4	3.0	
I _R	Leakage Current	V _R = 600V		10	100	μA
		V _R = 600V T _J = 175°C		5	200	

DYNAMIC CHARACTERISTICS (T_C = 25°C unless otherwise stated Per Side)

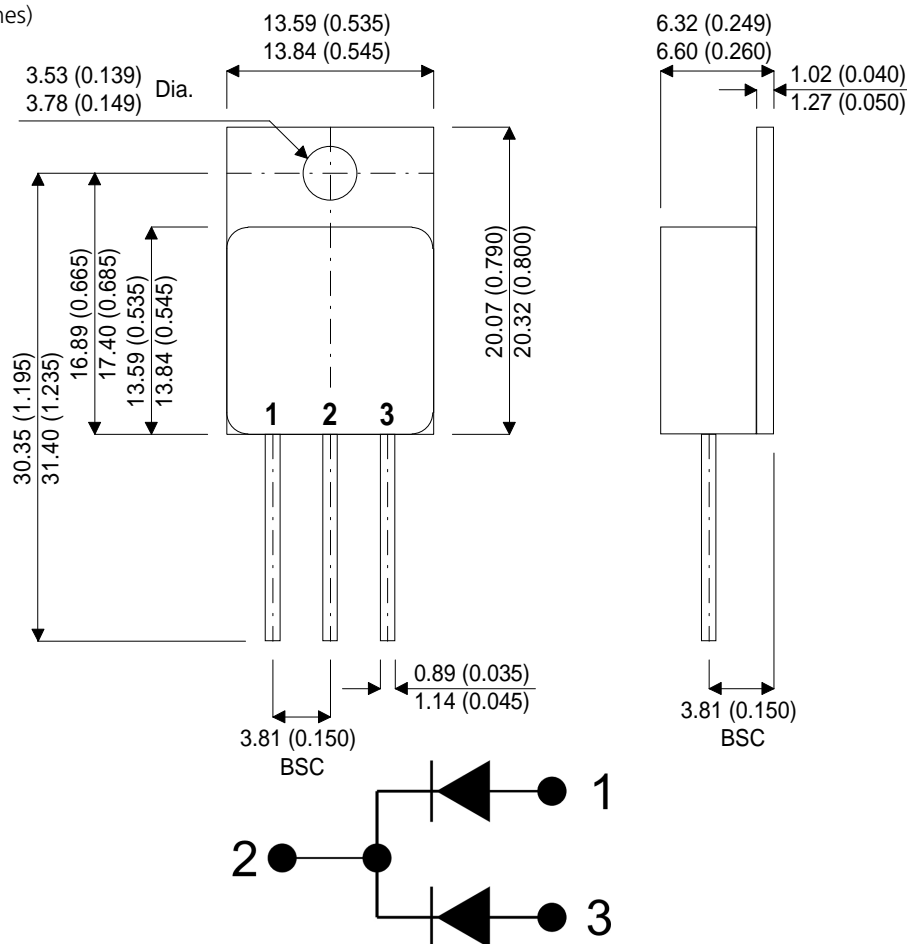
C	Total Capacitance	V _R = 1.0V	f = 1.0MHz		700	pF
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Notes

(1) Pulse Width ≤ 300us, δ ≤ 2%

MECHANICAL DATA

Dimensions in mm (inches)



(TO-254AA) METAL PACKAGE

Pad 1 - Anode 1

Pad 2 - Cathode

Pad 3 - Anode 2